



Model No. PDT-A85A30
850nm GaAs PIN Photodiode in TO-46 Package for 850nm Emitter

FEATURES

- Industry standard TO-46 package with cap lens
- Optimized for fiber optic application
- High coupling efficiency to multi-mode fibers directly
- Low dark current and low capacitance
- Bandwidth >1.5 GHz



ELECTRO-OPTICAL CHARACTERISTICS

PARAMETERS	SYMBOL	MIN	TYP	MAX	UNIT	TEST CONDITIONS
Responsivity ⁽¹⁾	R	-	0.3	0.4	A/W	V _R =5V, λ = 850 nm
Forward Current	I _F	100	-	-	μA	V _F =1V
Dark Current	I _D	-	1	2	nA	V _R =5V
Breakdown Voltage	V _{BD}	-	85	-	V	I _R =10μA
Capacitance ⁽²⁾	C	-	1.2	1.5	pF	V _R =5V, f=1 MHz

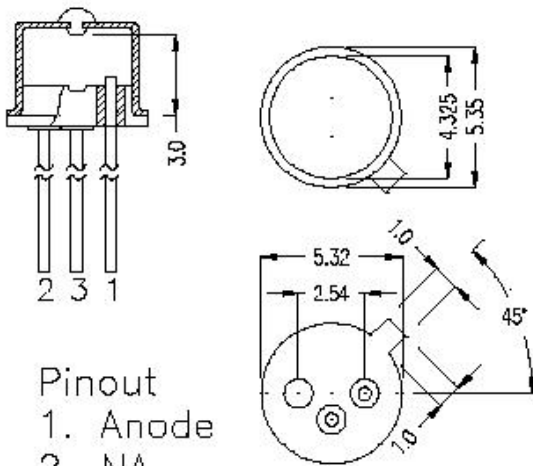
Notes:

1. The responsivity is measured with a receptacle package, using an 850 nm VCSEL as the optical light source to the 50/125 or 62.5/125 μm multi-mode fibers.
2. Sensitive area is typical 120μm in diameter.

ABSOLUTE MAXIMUM RATINGS

PARAMETERS	MIN	MAX	UNIT	CONDITIONS
Storage Temperature	-40	125	°C	
Operating Temperature	-20	85	°C	
Lead Solder Temperature		260	°C	10 seconds

OUTLINE DIMENSIONS (unit: mm)



Pinout
 1. Anode
 2. NA
 3. Cathode





TYPICAL CHARACTERISTICS

Fig. 1 Typical Dark Current and Forward Current

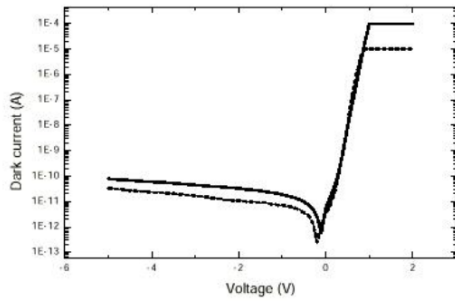


Fig. 2 Typical Photo-Current

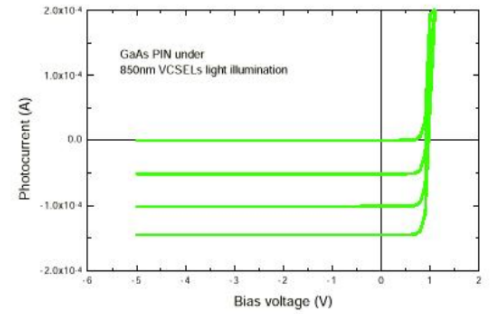


Fig. 3 Typical Breakdown Curve

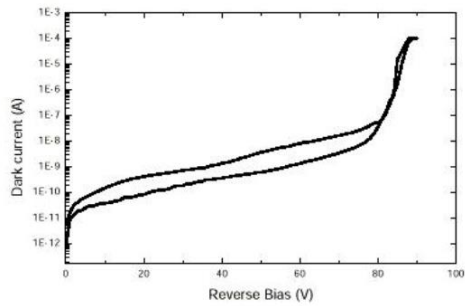
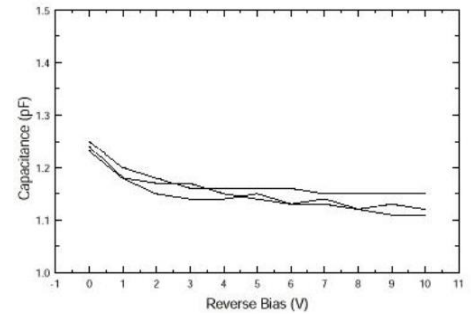


Fig. 4 Typical C-V Curve



Note: The above specifications are subject to change without notice.

